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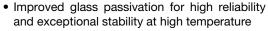
Vishay Semiconductors

Medium Power Phase Control Thyristors (Stud Version), 22 A



PRIMARY CHARACTERISTICS				
I _{T(AV)}	22 A			
V _{DRM} /V _{RRM}	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V			
V_{TM}	1.70 V			
I _{GT}	60 mA			
T _J	-65 °C to +125 °C			
Package	TO-48 (TO-208AA)			
Circuit configuration	Single SCR			

FEATURES





- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- Medium power switching
- · Phase control applications

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		22	A		
$I_{T(AV)}$	T _C	85	°C		
I _{T(RMS)}		35	A		
I _{TSM}	50 Hz	400	۸		
	60 Hz	420	A		
l ² t	50 Hz	793	— A ² s		
	60 Hz	724	A-s		
V _{DRM} /V _{RRM}		100 to 1200	V		
tq	Typical	110	μs		
T _J		-65 to +125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE	VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA				
	10	100	150	20				
	20	200	300					
	40	400	500					
VS-22RIA	60	600	700	10				
	80	800	900	10				
	100	1000	1100					
	120	1200	1300					

Notes

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

⁽²⁾ For voltage pulses with $t_p \le 5$ ms



PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current	I	190° cinus	180° sinusoidal conduction		22	А
at case temperature	I _{T(AV)}	100 5111050	ndar conduction		85	°C
Maximum RMS on-state current	I _{T(RMS)}				35	Α
		t = 10 ms	No voltage		400	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		420	1
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		335	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	355	1
Maximum I ² t for fusing		t = 10 ms	No voltage	initial T _J =T _J maximum	793	A ² s
	l ² t	t = 8.3 ms	reapplied		724	
		t = 10 ms	100 % V _{RRM}		560	
		t = 8.3 ms	reapplied		515	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		7930	A²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		0.83	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		ium	0.95	, v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		14.9		
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		13.4	- mΩ	
Maximum on-state voltage	V _{TM}	I _{pk} = 70 A, T _J = 25 °C			1.70	V
Maximum holding current	I _H	T 05 °C	anada ayanbi C	V registive lead	130	A
Latching current	ΙL	$I_{\rm J} = 25^{-1}{\rm C},$	T _J = 25 °C, anode supply 6 V, resistive load			mA

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
	$V_{DRM} \le 600 \text{ V}$			200	
Maximum rate of rise	$V_{DRM} \le 800 \text{ V}$	dl/dt	T_J = T_J maximum, V_{DM} = Rated V_{DRM} Gate pulse = 20 V, 15 Ω , t_p = 6 μ s, t_r = 0.1 μ s maximum I_{TM} = (2 x rated dl/dt) A	180	A/μs
of turned-on current	$V_{DRM} \le 1000 \text{ V}$			160	
	$V_{DRM} \le 1600 \text{ V}$			150	
Typical turn-on time		t _{gt}	$T_J = 25$ °C, at rated V_{DRM}/V_{RRM} , $T_J = 125$ °C	0.9	
Typical reverse recovery time		t _{rr}	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, $t_p > 200 \ \mu s$, $dI/dt = -10 \ A/\mu s$	4	μs
Typical turn-off time		t _q	$T_J=T_J$ maximum, $I_{TM}=I_{T(AV)},t_p>200~\mu s,V_R=100~V,dI/dt=$ - 10 A/µs, dV/dt = 20 V/µs linear to 67 % $V_{DRM},$ gate bias 0 V to 100 W	110	μ

Note

• $t_q = 10 \mu s$ up to 600 V, $t_q = 30 \mu s$ up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	T _J = T _J maximum linear to 100 % rated V _{DRM}	100	V/µs
of off-state voltage	uv/ut	T _J = T _J maximum linear to 67 % rated V _{DRM}	300 (1)	ν/μδ

Note

(1) Available with: $dV/dt = 1000 V/\mu s$, to complete code add S90 i.e. 22RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TES	T CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}	$T_{il} = T_{il}$ maximum		8.0	W
Maximum average gate power	P _{G(AV)}	T j = T j maximum		2.0	vv
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum		1.5	Α
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum		10	V
		T _J = - 65 °C		90	
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units	60	mA
		T _J = 125 °C		35	
	V _{GT}	T _J = - 65 °C		3.0	V
DC gate voltage required to trigger		T _J = 25 °C	6 V anode to cathode applied	2.0	
		T _J = 125 °C		1.0	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum, V _{DRM} = Rated value		2.0	mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J \text{ maximum},$ $V_{DRM} = \text{Rated value}$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	٧

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VAL	VALUES	
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-65 to	-65 to +125	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation 0.86		K/W	
Maximum thermal resistance, case to heat sink	R _{thCS}	Mounting surface, smooth, flat and greased 0.35			
			TO NUT	TO DEVICE	
			20 (27.5)	25	lbf ⋅ in
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf · m
		(1011 1021104 111 3023)		2.8	N · m
Approximate weight			1	4	g
Approximate weight			0.	49	OZ.
Case style		See dimensions - link at the end of datasheet	TO-48 (TO-208AA)		A)

△R _{thJC} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS		
180°	0.21	0.15				
120°	0.25	0.25				
90°	0.31	0.34	$T_J = T_J$ maximum	K/W		
60°	0.45	0.47				
30°	0.76	0.76				

Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

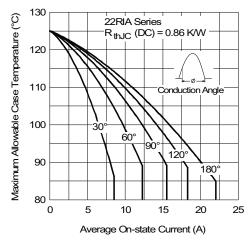


Fig. 1 - Current Ratings Characteristics

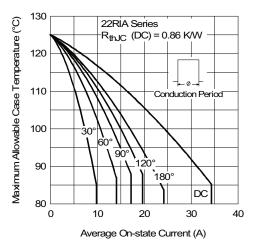


Fig. 1 - Current Ratings Characteristics

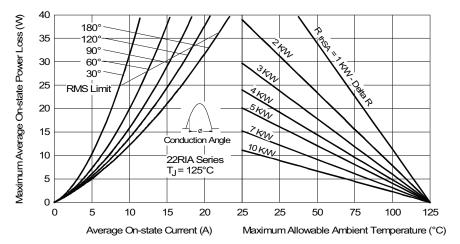


Fig. 2 - On-State Power Loss Characteristics

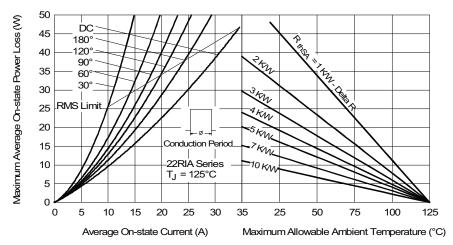


Fig. 3 - On-State Power Loss Characteristics

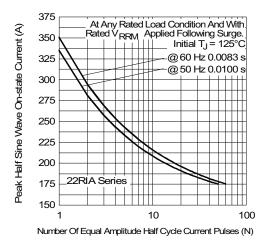


Fig. 4 - Maximum Non-Repetitive Surge Current

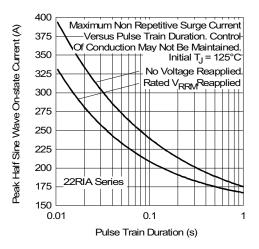


Fig. 5 - Maximum Non-Repetitive Surge Current

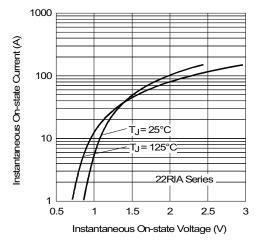


Fig. 6 - Forward Voltage Drop Characteristics

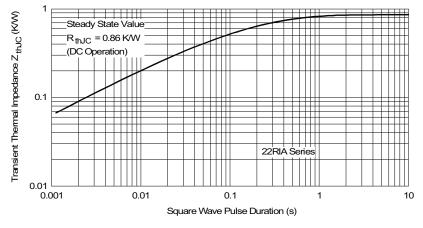


Fig. 7 - Thermal Impedance Z_{thJC} Characteristics

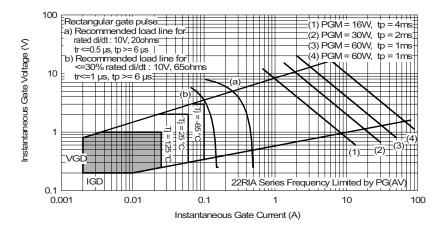
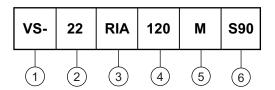


Fig. 8 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current code

3 - Essential part number

Voltage code x 10 = V_{RRM} (see Voltage Ratings table)

5 - None = stud base TO-48 (TO-208AA) 1/4" 28UNF-2A

M = stud base TO-48 (TO-208AA) M6 x 1

6 - Critical dV/dt:

None = 300 V/µs (standard value)

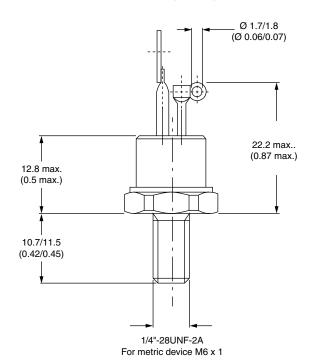
S90 = 1000 V/µs (special selection)

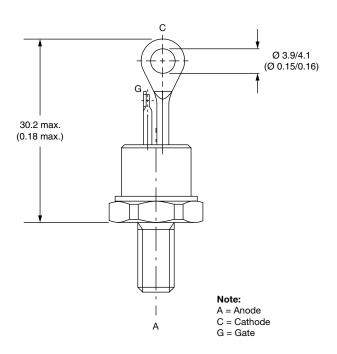
LINKS TO RELAT	TED DOCUMENTS
Dimensions	www.vishay.com/doc?95333

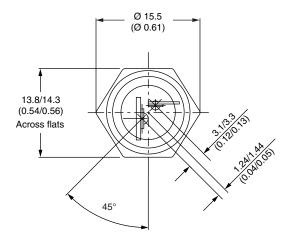


TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)









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